

512K x 8 HIGH-SPEED CMOS STATIC RAM

JANUARY 2025

FEATURES

HIGH SPEED: (IS61/64C5128AL)

- High-speed access time: 10ns, 12 ns
- Low Active Power: 150 mW (typical)
- Low Standby Power: 10 mW (typical)
CMOS standby

LOW POWER: (IS61/64C5128AS)

- High-speed access time: 25ns
- Low Active Power: 75 mW (typical)
- Low Standby Power: 1 mW (typical)
CMOS standby
- TTL compatible interface levels
- Single 5V ± 10% power supply
- Fully static operation: no clock or refresh required
- Available in 32-pin sTSOP-I, 32-pin SOP, 44-pin TSOP-II and 32-pin TSOP-II packages
- Commercial, Industrial and Automotive temperature ranges available
- Lead-free available

DESCRIPTION

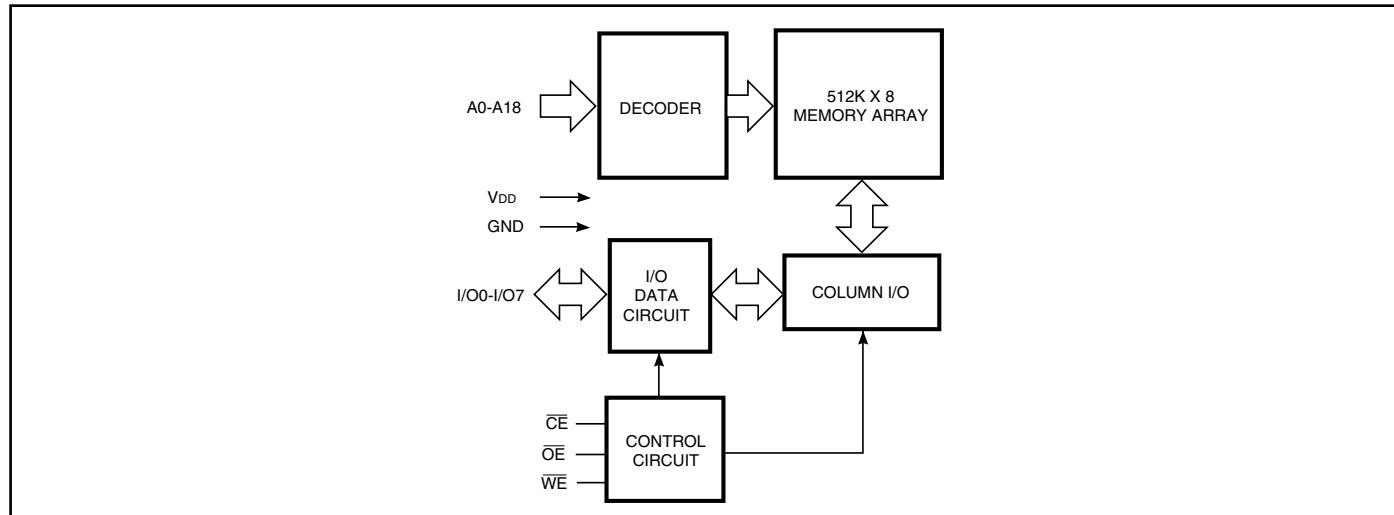
The *ISSI* IS61C5128AL/AS and IS64C5128AL/AS are high-speed, 4,194,304-bit static RAMs organized as 524,288 words by 8 bits. They are fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields access times as fast as 12 ns with low power consumption.

When \overline{CE} is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs, \overline{CE} and \overline{OE} . The active LOW Write Enable (WE) controls both writing and reading of the memory. A data byte allows Upper Byte (UB) and Lower Byte (LB) access.

The IS61C5128AL/AS and IS64C5128AL/AS are packaged in the JEDEC standard 32-pin sTSOP-I, 32-pin SOP, 44-pin TSOP-II and 32-pin TSOP-II packages

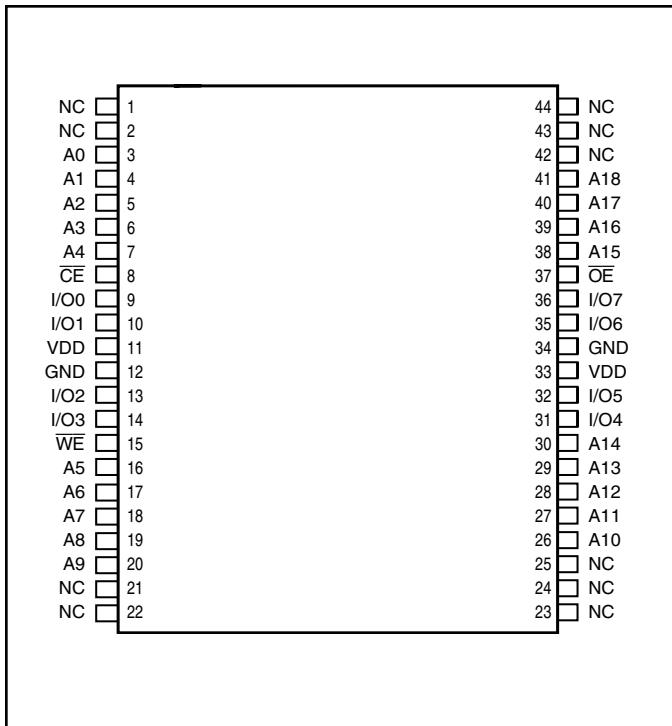
FUNCTIONAL BLOCK DIAGRAM



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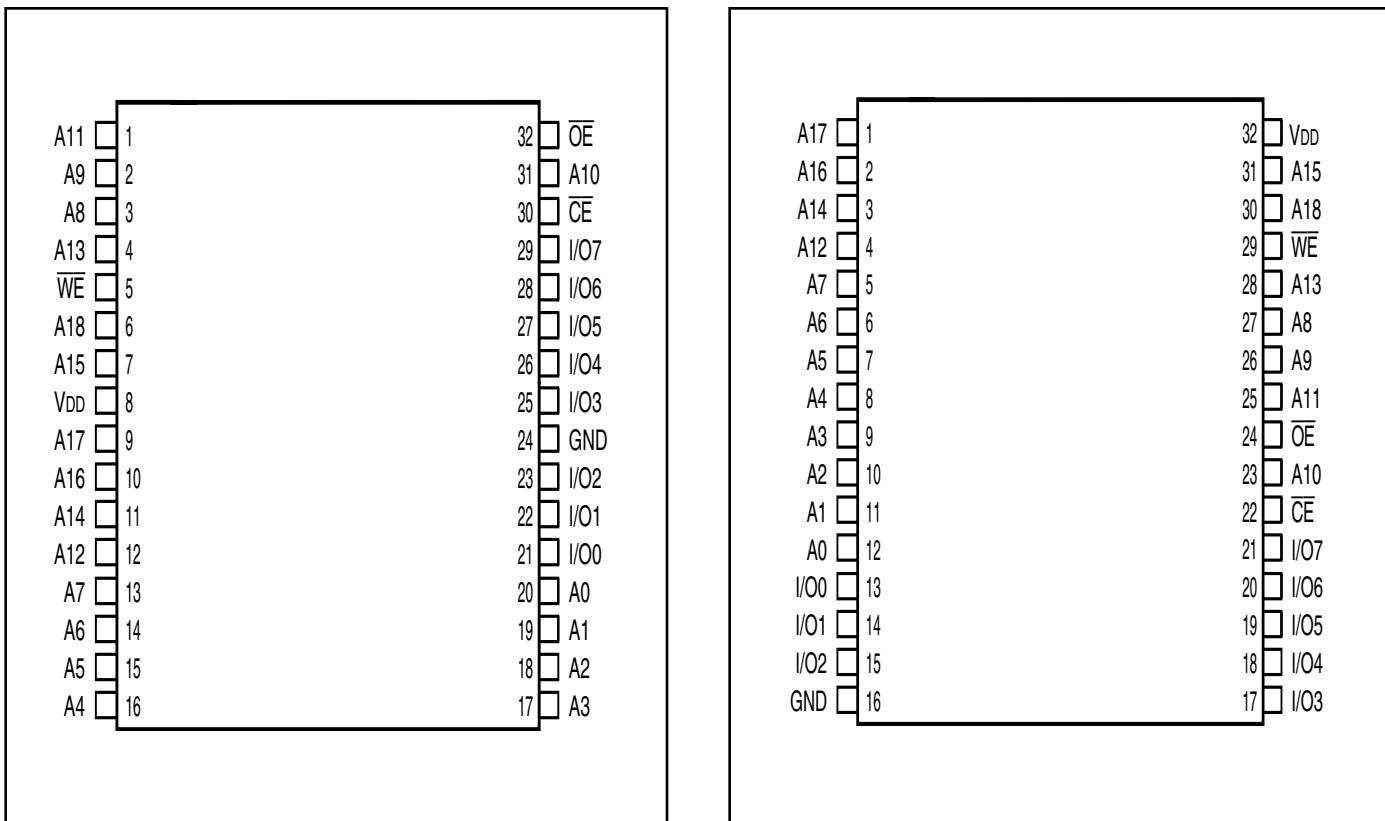
- a.) the risk of injury or damage has been minimized;
- b.) the user assume all such risks; and
- c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

HIGH SPEED (IS61/64C5128AL) PIN CONFIGURATION**44-Pin TSOP (Type II)****PIN DESCRIPTIONS**

A0-A18	Address Inputs
CE	Chip Enable Input
OE	Output Enable Input
WE	Write Enable Input
I/O0-I/O7	Bidirectional Ports
VDD	Power
GND	Ground
NC	No Connection

LOW POWER (IS61/64C5128AS) PIN CONFIGURATION

32-pin sTSOP (TYPE I)

32-pin SOP
32-pin TSOP (TYPE II)**PIN DESCRIPTIONS**

A0-A18 Address Inputs

CE Chip Enable 1 Input

OE Output Enable Input

WE Write Enable Input

I/O0-I/O7 Input/Output

VDD Power

GND Ground

IS61C5128AL/AS IS64C5128AL/AS**TRUTH TABLE**

Mode	WE	CE	OE	I/O PIN	
				I/O0-I/O7	V _{DD} Current
Not Selected	X	H	X	High-Z	I _{SB1} , I _{SB2}
Output Disabled	H	L	H	High-Z	I _{CC1} , I _{CC2}
Read	H	L	L	D _{OUT}	I _{CC1} , I _{CC2}
Write	L	L	X	D _{IN}	I _{CC1} , I _{CC2}

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V _{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
T _{STG}	Storage Temperature	-65 to +150	°C
P _T	Power Dissipation	1.5	W
I _{OUT}	DC Output Current (LOW)	20	mA

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	5	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	7	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 5.0V.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{DD} = Min., I _{OH} = -4.0 mA	2.4	—	V
V _{OL}	Output LOW Voltage	V _{DD} = Min., I _{OL} = 8.0 mA	—	0.4	V
V _{IH}	Input HIGH Voltage		2.2	V _{DD} + 0.5	V
V _{IL}	Input LOW Voltage ⁽¹⁾		-0.3	0.8	V
I _{LI}	Input Leakage	GND ≤ V _{IN} ≤ V _{DD}	Com. Ind. Auto.	-1 -2 -5	μA
I _{LO}	Output Leakage	GND ≤ V _{OUT} ≤ V _{DD} Outputs Disabled	Com. Ind. Auto.	-1 -2 -5	μA

Note: 1. V_{IL} = -3.0V for pulse width less than 10 ns.

OPERATING RANGE: HIGH SPEED OPTION (IS61/64C5128AL)

Range	Ambient Temperature	V _{DD}	Speed (ns)
Commercial	0°C to +70°C	5V ± 10%	10
Industrial	-40°C to +85°C	5V ± 10%	10
Automotive	-40°C to +125°C	5V ± 10%	12

OPERATING RANGE: LOW POWER OPTION (IS61/64C5128AS)

Range	Ambient Temperature	V _{DD}	Speed (ns)
Commercial	0°C to +70°C	5V ± 10%	25
Industrial	-40°C to +85°C	5V ± 10%	25
Automotive	-40°C to +125°C	5V ± 10%	25

HIGH SPEED OPTION (IS61/64C5128AL)
POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions	-10 ns		-12 ns		Unit
			Min.	Max.	Min.	Max.	
Icc1	V _{DD} Operating Supply Current	V _{DD} = V _{DD} MAX., $\overline{CE} = V_{IL}$	Com.	—	45	—	45
		I _{OUT} = 0 mA, f = 0	Ind.	—	50	—	50
			Auto.	—	55	—	55
Icc2	V _{DD} Dynamic Operating Supply Current	V _{DD} = V _{DD} MAX., $\overline{CE} = V_{IL}$	Com.	—	50	—	45
		I _{OUT} = 0 mA, f = f _{MAX}	Ind.	—	55	—	50
			Auto.	—	70	—	60
			typ. ⁽²⁾	30		25	
IsB1	TTL Standby Current (TTL Inputs)	V _{DD} = V _{DD} MAX.,	Com.	—	15	—	15
		V _{IN} = V _{IH} or V _{IL}	Ind.	—	20	—	20
		$\overline{CE} \geq V_{IH}$, f = 0	Auto.	—	30	—	30
IsB2	CMOS Standby Current (CMOS Inputs)	V _{DD} = V _{DD} MAX.,	Com.	—	8	—	8
		$\overline{CE} \leq V_{DD} - 0.2V$,	Ind.	—	12	—	12
		V _{IN} ≥ V _{DD} - 0.2V, or	Auto.	—	20	—	20
		V _{IN} ≤ 0.2V, f = 0	typ. ⁽²⁾	2			

Note:

1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
2. Typical values are measured at V_{DD} = 5V, T_A = 25% and not 100% tested.

LOW POWER OPTION (IS61/64C5128AS)
POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions	-25 ns		Unit
			Min.	Max.	
Icc	Average operating Current	$\overline{CE} = V_{IL}$, V _{DD} = Max.	Com.	—	10
		I _{OUT} = 0 mA, f = 0	Ind.	—	15
			Auto.	—	20
Icc1	V _{DD} Dynamic Operating Supply Current	V _{DD} = Max., $\overline{CE} = V_{IL}$	Com.	—	25
		I _{OUT} = 0 mA, f = f _{MAX}	Ind.	—	30
			Auto.	—	40
			typ. ⁽²⁾	15	
IsB1	TTL Standby Current (TTL Inputs)	V _{DD} = Max.,	Com.	—	1
		V _{IN} = V _{IH} or V _{IL} , $\overline{CE} \geq V_{IH}$,	Ind.	—	1.5
		f = 0	Auto.	—	2
IsB2	CMOS Standby Current (CMOS Inputs)	V _{DD} = Max.,	Com.	—	0.8
		$\overline{CE} \geq V_{DD} - 0.2V$,	Ind.	—	0.9
		V _{IN} ≥ V _{DD} - 0.2V,	Auto.	—	2
		or V _{IN} ≤ V _{SS} + 0.2V, f = 0	typ.	0.2	

Note:

1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
2. Typical values are measured at V_{DD} = 5V, T_A = 25% and not 100% tested.

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	-10		-12		-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t _{RC}	Read Cycle Time	10	—	12	—	25	—	ns
t _{AA}	Address Access Time	—	10	—	12	—	25	ns
t _{OH}	Output Hold Time	3	—	3	—	3	—	ns
t _{ACE}	CE Access Time	—	10	—	12	—	25	ns
t _{DOE}	OE Access Time	—	5	—	6	—	15	ns
t _{HZOE} ⁽²⁾	OE to High-Z Output	0	5	0	6	0	8	ns
t _{LZOE} ⁽²⁾	OE to Low-Z Output	0	—	0	—	2	—	ns
t _{HZCE} ⁽²⁾	CE to High-Z Output	0	5	0	6	0	8	ns
t _{LZCE} ⁽²⁾	CE to Low-Z Output	2	—	2	—	2	—	ns

Notes:

- Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
- Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
- Not 100% tested.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

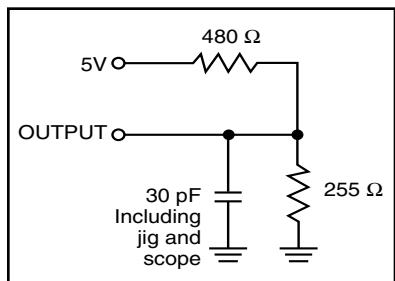
AC TEST LOADS

Figure 1

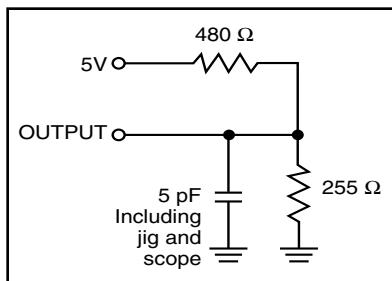
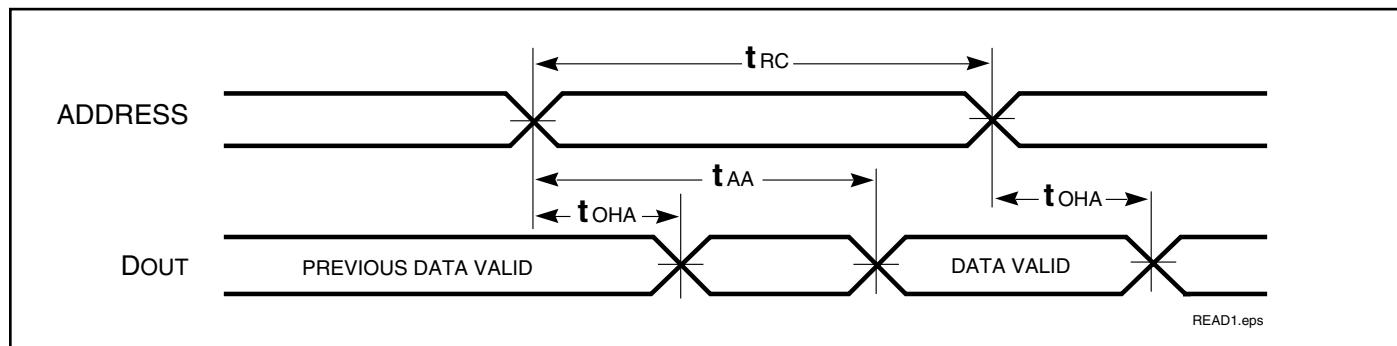


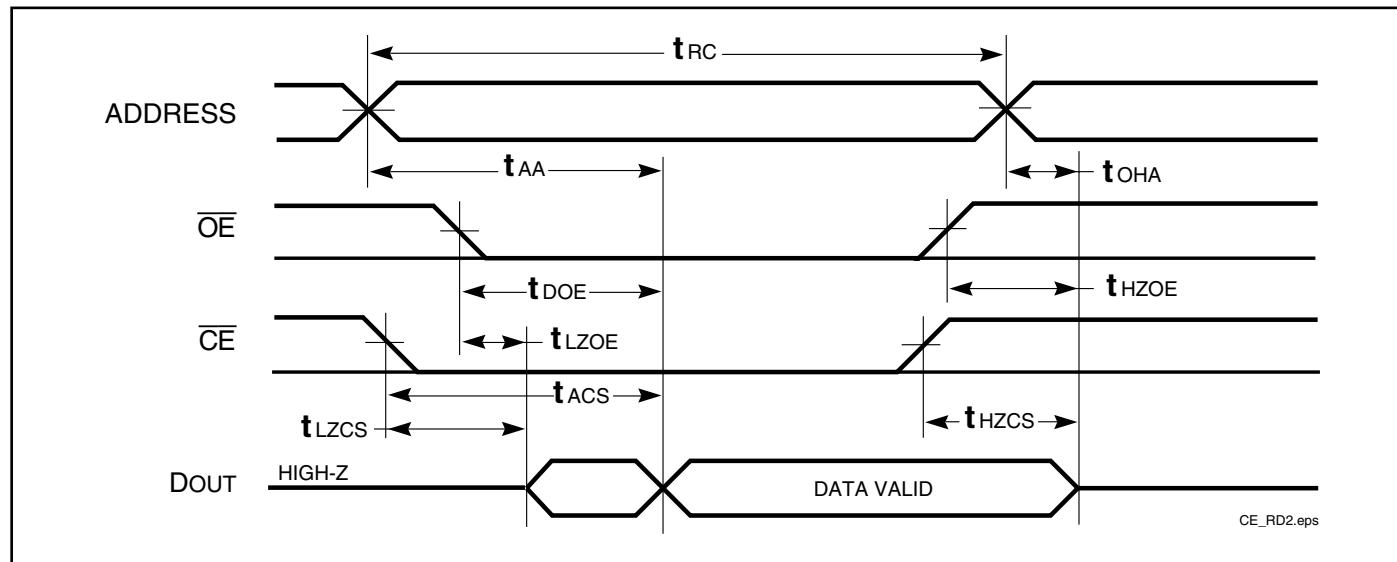
Figure 2

AC WAVEFORMS

READ CYCLE NO. 1^(1,2)



READ CYCLE NO. 2^(1,3)



Notes:

1. \overline{WE} is HIGH for a Read Cycle.
2. The device is continuously selected. \overline{OE} , \overline{CE} = V_{IL} .
3. Address is valid prior to or coincident with \overline{CE} LOW transitions.

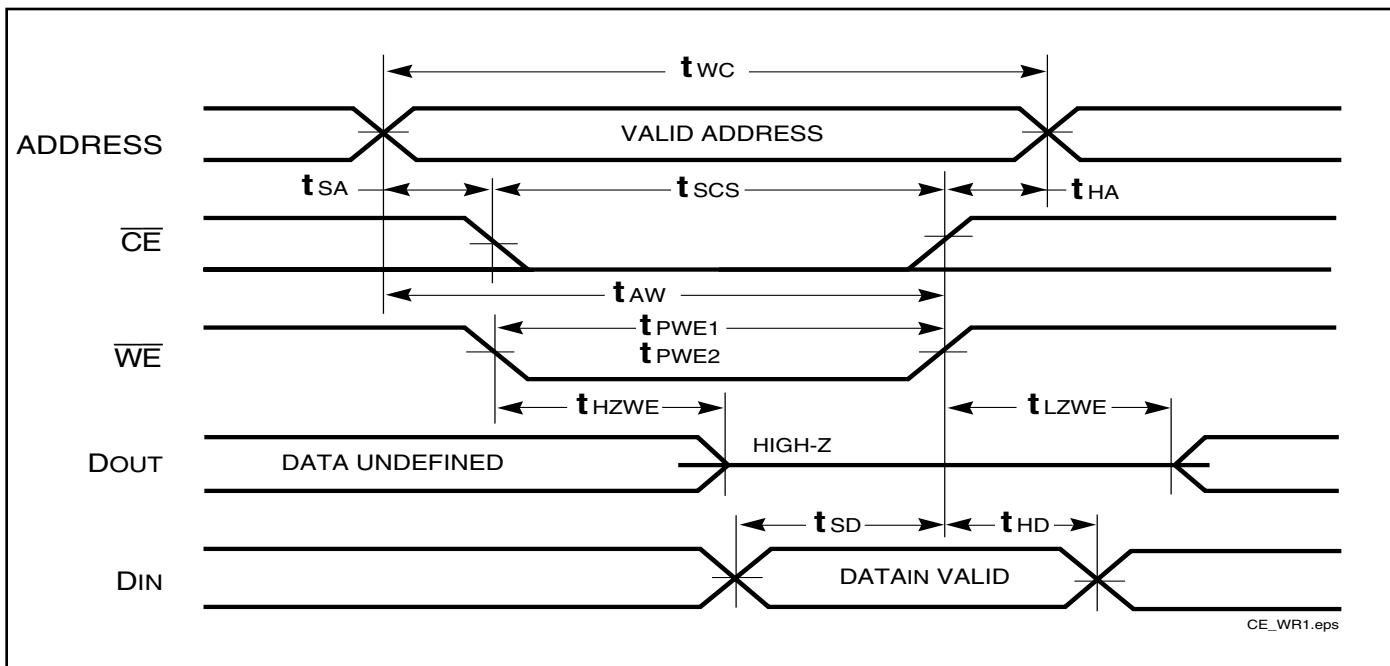
WRITE CYCLE SWITCHING CHARACTERISTICS^(1,3) (Over Operating Range)

Symbol	Parameter	-10		-12		-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t _{WC}	Write Cycle Time	10	—	12	—	25	—	ns
t _{SCE}	CE to Write End	7	—	9	—	18	—	ns
t _{AW}	Address Setup Time to Write End	7	—	9	—	18	—	ns
t _{HA}	Address Hold from Write End	0	—	0	—	0	—	ns
t _{SA}	Address Setup Time	0	—	0	—	0	—	ns
t _{PWE1}	WE Pulse Width (OE =High)	7	—	9	—	15	—	ns
t _{PWE2}	WE Pulse Width (OE=Low)	7	—	9	—	15	—	ns
t _{SD}	Data Setup to Write End	6	—	6	—	15	—	ns
t _{HD}	Data Hold from Write End	0	—	0	—	0	—	ns
t _{HZWE⁽²⁾}	WE LOW to High-Z Output	—	6	—	6	—	15	ns
t _{LZWE⁽²⁾}	WE HIGH to Low-Z Output	3	—	3	—	5	—	ns

Notes:

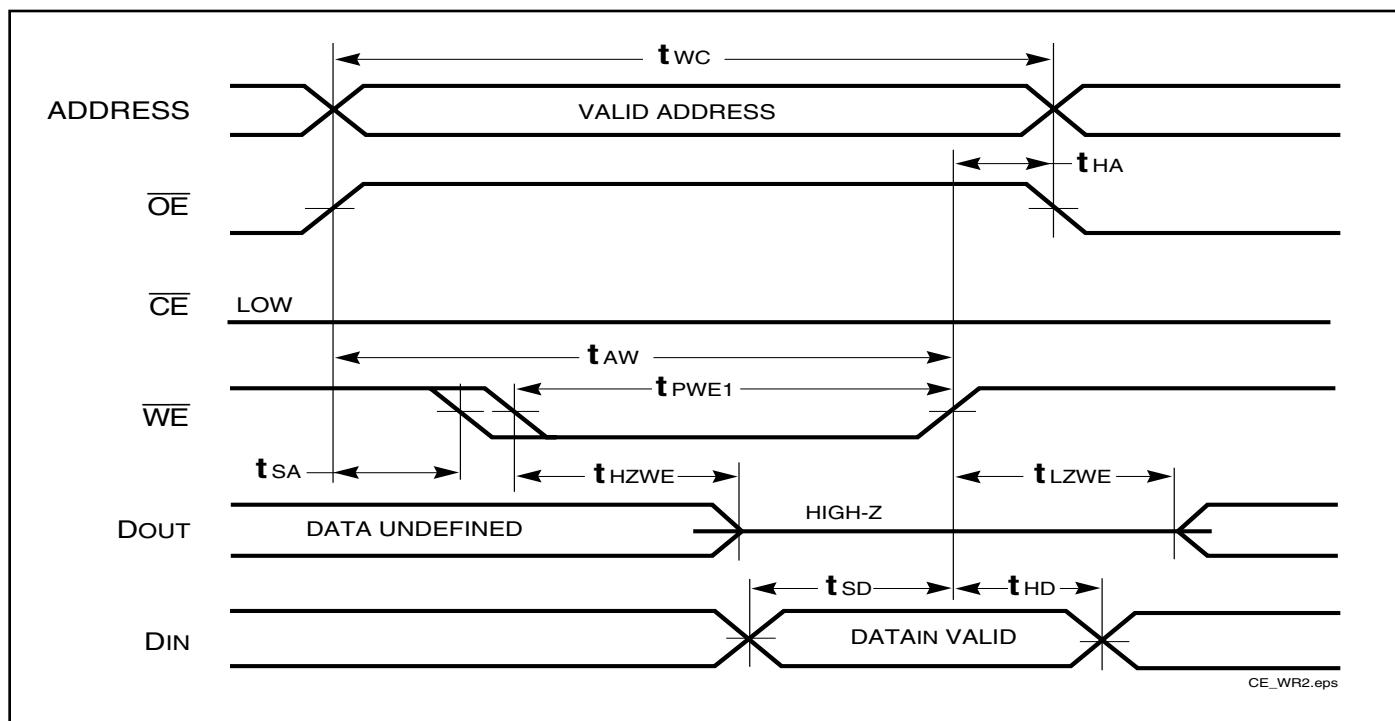
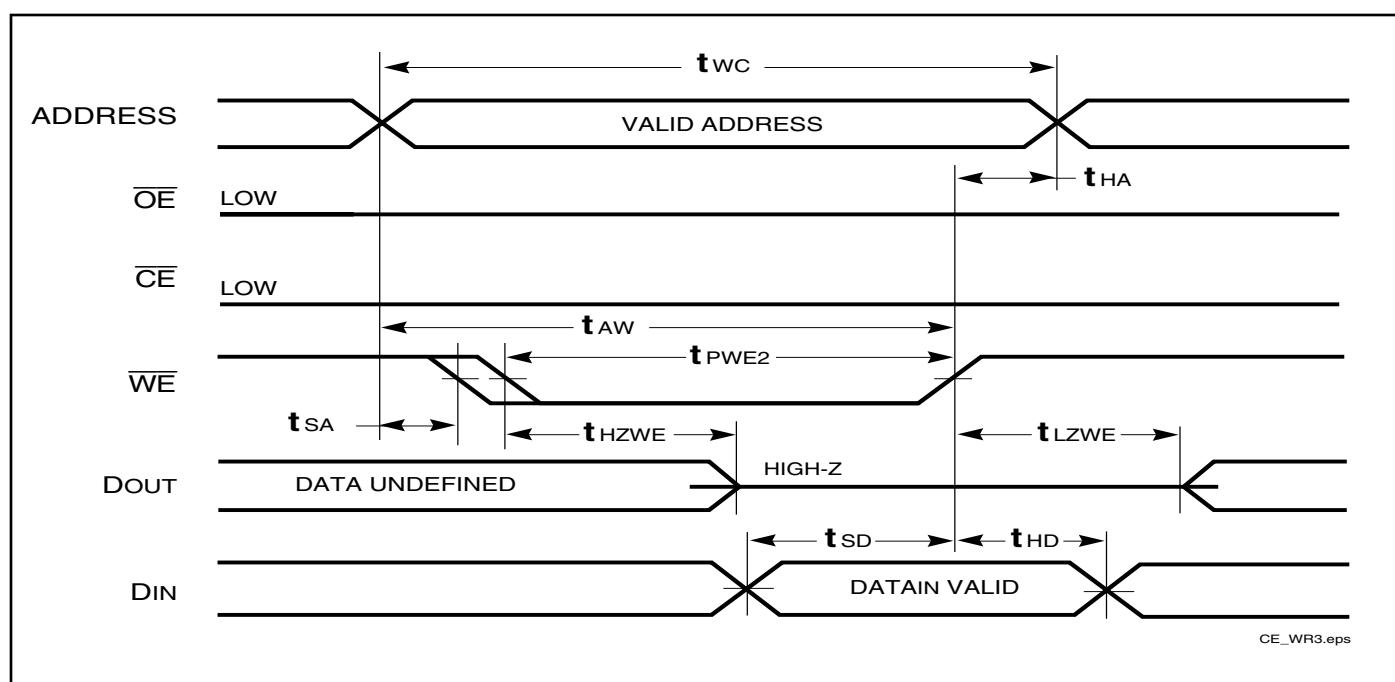
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of CE LOW, and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.

AC WAVEFORMS

WRITE CYCLE NO. 1 (\overline{WE} Controlled)^(1,2)

Notes:

1. The internal write time is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if $\overline{OE} \geq V_{IH}$.

WRITE CYCLE NO. 2 (\overline{OE} is HIGH During Write Cycle) ^(1,2)WRITE CYCLE NO. 3 (\overline{OE} is LOW During Write Cycle) ⁽¹⁾

Notes:

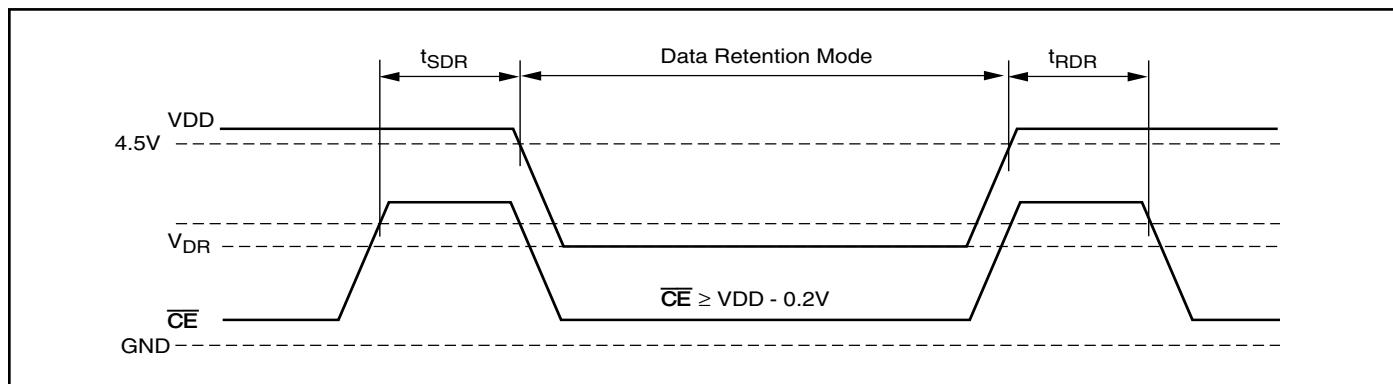
1. The internal write time is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if $\overline{OE} \geq V_{IH}$.

DATA RETENTION SWITCHING CHARACTERISTICS (HIGH SPEED) (IS61/64C5128AL)

Symbol	Parameter	Test Condition	Min.	Max.	Unit
V_{DR}	V_{DD} for Data Retention	See Data Retention Waveform	2.9	5.5	V
I_{DR}	Data Retention Current	$V_{DD} = 2.9V, \overline{CE} \geq V_{DD} - 0.2V$	—	8	mA
		$V_{IN} \geq V_{DD} - 0.2V$, or $V_{IN} \leq V_{SS} + 0.2V$	Com. Ind.	—	10
			Auto. typ. ⁽¹⁾	—	15
t_{SDR}	Data Retention Setup Time	See Data Retention Waveform	0	—	ns
t_{RDR}	Recovery Time	See Data Retention Waveform	t_{RC}	—	ns

Note:

1. Typical Values are measured at $V_{DD} = 5V$, $T_A = 25^\circ C$ and not 100% tested.

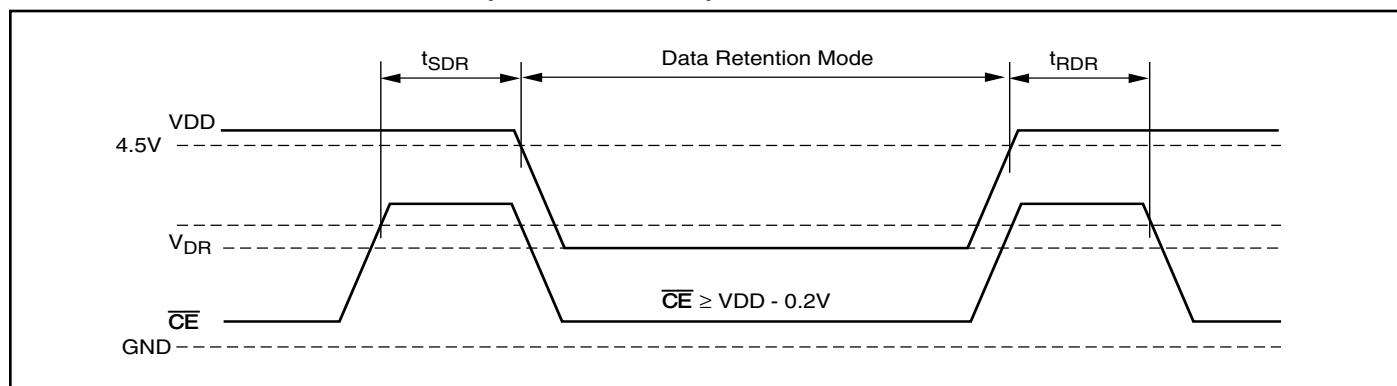
DATA RETENTION WAVEFORM (\overline{CE} Controlled)

DATA RETENTION SWITCHING CHARACTERISTICS (LOW POWER) (IS61/64C5128AS)

Symbol	Parameter	Test Condition	Min.	Max.	Unit
V_{DR}	VDD for Data Retention	See Data Retention Waveform	2.9	5.5	V
I_{DR}	Data Retention Current	$V_{DD} = 2.9V, \overline{CE} \geq V_{DD} - 0.2V$	—	0.8	mA
		$V_{IN} \geq V_{DD} - 0.2V$, or $V_{IN} \leq V_{SS} + 0.2V$	Com. Ind.	—	0.9
		Auto. typ. ⁽¹⁾	—	2	
t_{SDR}	Data Retention Setup Time	See Data Retention Waveform	0	—	ns
t_{RDR}	Recovery Time	See Data Retention Waveform	t_{RC}	—	ns

Note:

1. Typical Values are measured at $V_{DD} = 5V$, $T_A = 25^\circ C$ and not 100% tested.

DATA RETENTION WAVEFORM (\overline{CE} Controlled)

HIGH SPEED (IS61/64C5128AL)**ORDERING INFORMATION****Industrial Range: -40°C to +85°C**

Speed (ns)	Order Part No.	Package
10	IS61C5128AL-10TLI	44-pin TSOP-II, green

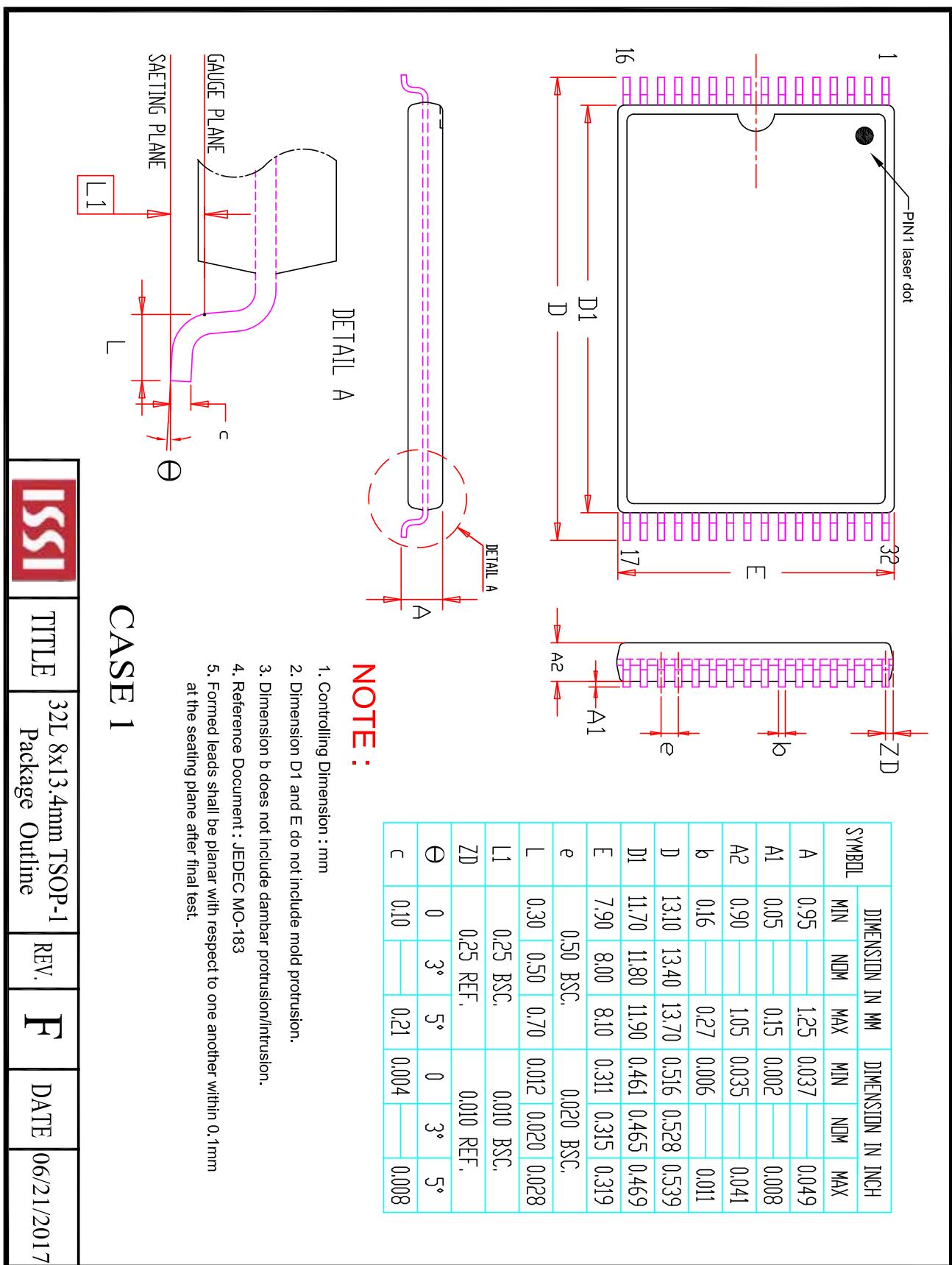
Automotive Range: -40°C to +125°C

Speed (ns)	Order Part No.	Package
12	IS64C5128AL-12CTLA3	44-pin TSOP-II, green, Copper Leadframe

LOW POWER (IS61/64C5128AS)**ORDERING INFORMATION****Industrial Range: -40°C to +85°C**

Speed (ns)	Order Part No.	Package
25	IS61C5128AS-25QLI	450-mil Plastic SOP, green
	IS61C5128AS-25HLI	32-pin STSOP-I, green
	IS61C5128AS-25TLI	32-pin TSOP-II, green

Note: All products listed above are green. This refers to the package being (RoHS Compliant, Halogen-free) and TSCA Compliant.



ISSI	TITLE	32L 8x13.4mm TSOP-1	REV.	F	DATE	06/21/2017
Rev. C2 01/15/2025						

